Abstracts

Some Aspects of GaAs MESFET Reliability

D.A. Abbott and J.A. Turner. "Some Aspects of GaAs MESFET Reliability." 1976 Transactions on Microwave Theory and Techniques 24.6 (Jun. 1976 [T-MTT] (Special Issue on Microwave Field-Effect Transistors)): 317-321.

The results of a short study into the reliability and failure modes of GaAs MESFET's are presented. Two failure modes have been observed during this study and improved fabrication techniques that reduce their occurrence have been examined. The results obtained indicate that extremely reliable devices can be manufactured with a predicted mean time to failure in excess of 10/sup 7/h at junction temperatures of 70°C. Room-temperature life tests in excess of 1/2 million device hours lend support to these predictions.

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